

# FMM5703VZ

## K / Ka Band Low Noise Amplifier MMIC

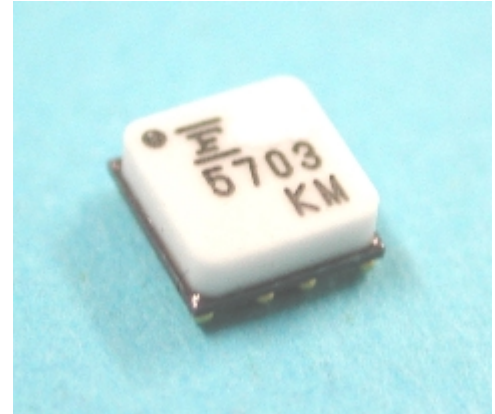
### FEATURES

- Low Noise Figure : NF = 2.5dB (typ.) @ f=32GHz
- High Associated Gain : Gas = 16dB (typ.) @f=32GHz
- Broad Band : 24~32GHz
- High Output Power : P<sub>1dB</sub> = 8dBm ( Typ. ) @f=32GHz
- Ball Grid Array SMT Package(VZ-pkg)
- Impedance Matched Z<sub>in</sub>/Z<sub>out</sub> = 50Ω

### DESCRIPTION

The FMM5703VZ is a LNA MMIC designed for applications in the 24~32 GHz frequency range. This product is well suited for fixed wireless access, radio link, and applications where low noise and high dynamic range are required.

Eudyna's stringent Quality Assurance Program assures the highest reliability and consistent performance.



### ABSOLUTE MAXIMUM RATING

Item	Symbol	Rating	Unit
Drain Voltage	VDD	4	V
Input Power	P <sub>in</sub>	-3	dBm
Storage Temperature	T <sub>stg</sub>	-55 to +125	°C

### RECOMMENDED OPERATING CONDITIONS

Item	Symbol	Condition	Unit
Drain Voltage	VDD	≤ 3	V
Operating Case Temperature	TC	-40 to +85	°C

### ELECTRICAL CHARACTERISTICS (Case Temperature T<sub>c</sub>=25°C)

Item	Symbol	Test Conditions	Limits			Unit
			Min.	Typ.	Max.	
Noise Figure	NF	f=32GHz	-	2.5	3	dB
Associated Gain	Gas	VDD=3V	14	16	19	dB
Output Power at 1dB G.C.P.	P <sub>1dB</sub>	I <sub>DD</sub> =20mA typ.	-	8.0	-	dBm
Input Return Loss (at P <sub>in</sub> =-20dBm)	RL <sub>in</sub>	Z <sub>S</sub> =Z <sub>L</sub> =50ohm	-	-10	-	dB
Output Return Loss (at P <sub>in</sub> =-20dBm)	RL <sub>out</sub>		-	-10	-	dB

G.C.P. : Gain Compression Point

ESD	Class 0	~ 199V
-----	---------	--------

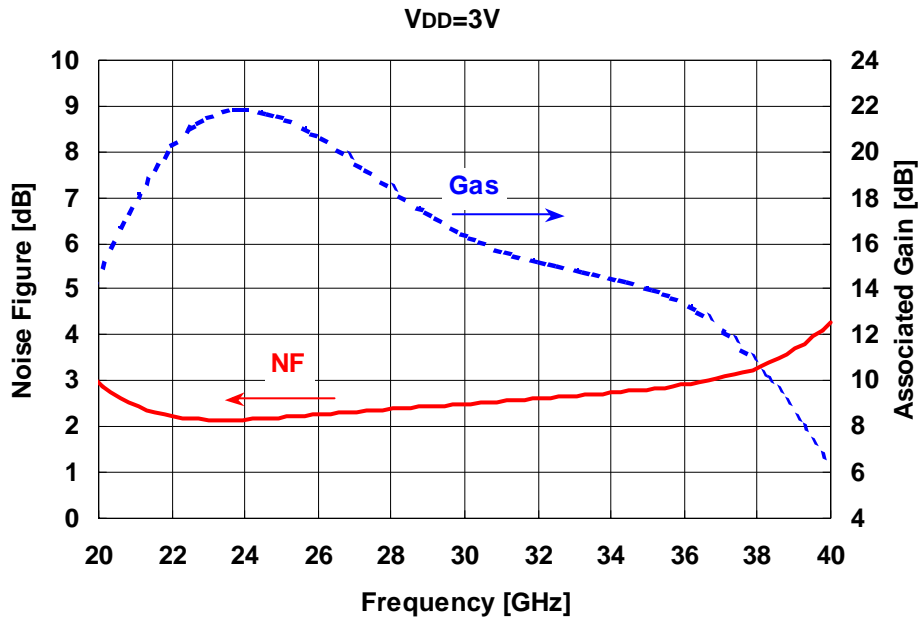
Note : Based on EIAJ ED-4701 C-111A(C=100pF, R=1.5kΩ)

CASE STYLE	VZ
------------	----

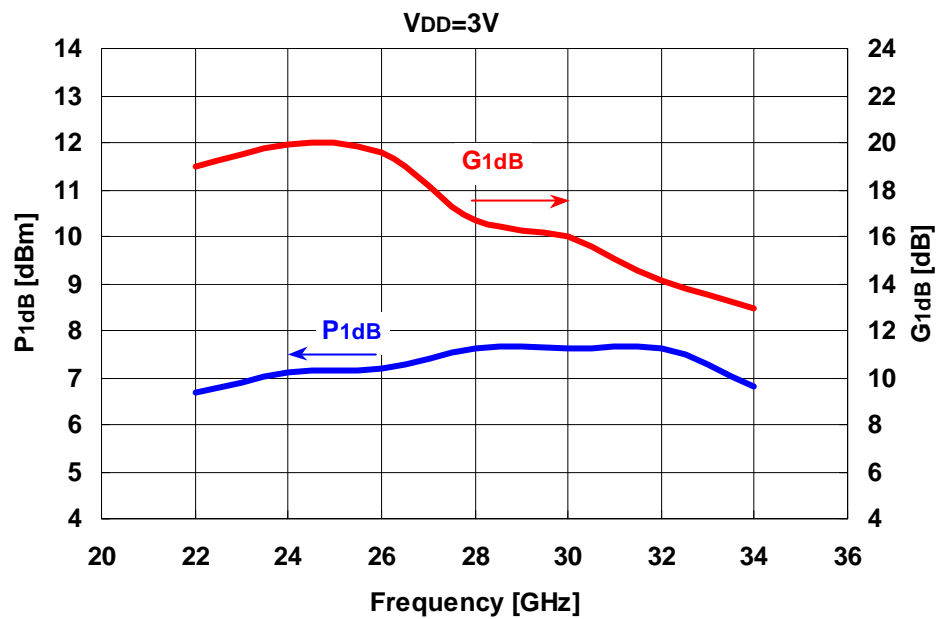
# FMM5703VZ

K / Ka Band Low Noise Amplifier MMIC

NOISE FIGURE, ASSOCIATED GAIN vs. FREQUENCY



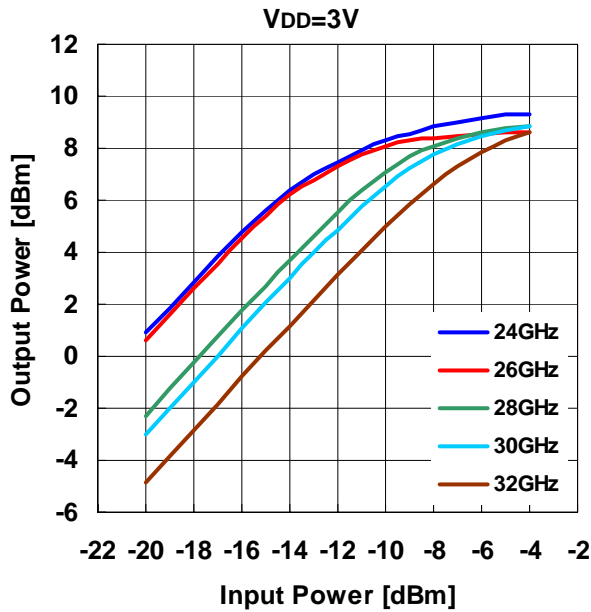
P<sub>1dB</sub>, G<sub>1dB</sub> vs. FREQUENCY



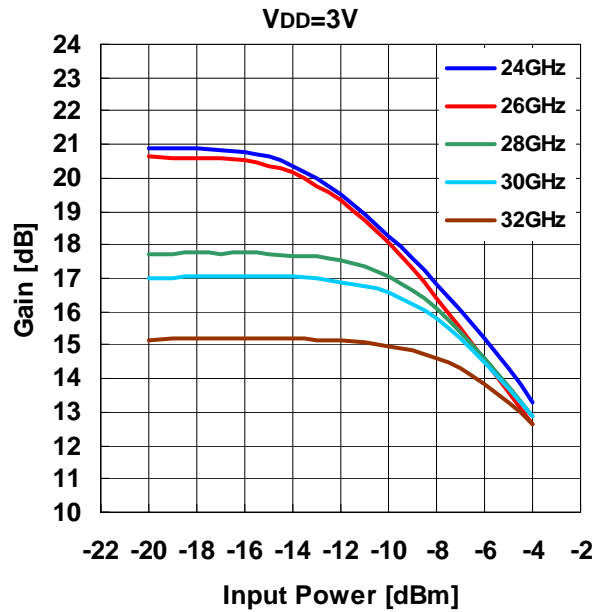
# FMM5703VZ

K / Ka Band Low Noise Amplifier MMIC

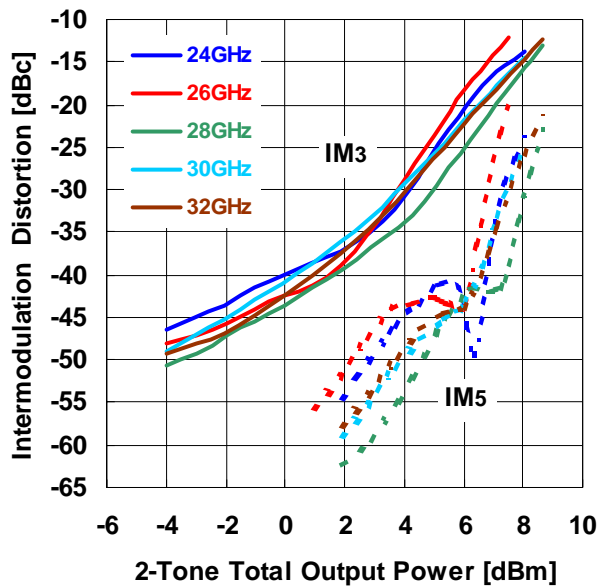
OUTPUT POWER vs. INPUT POWER



GAIN vs. INPUT POWER



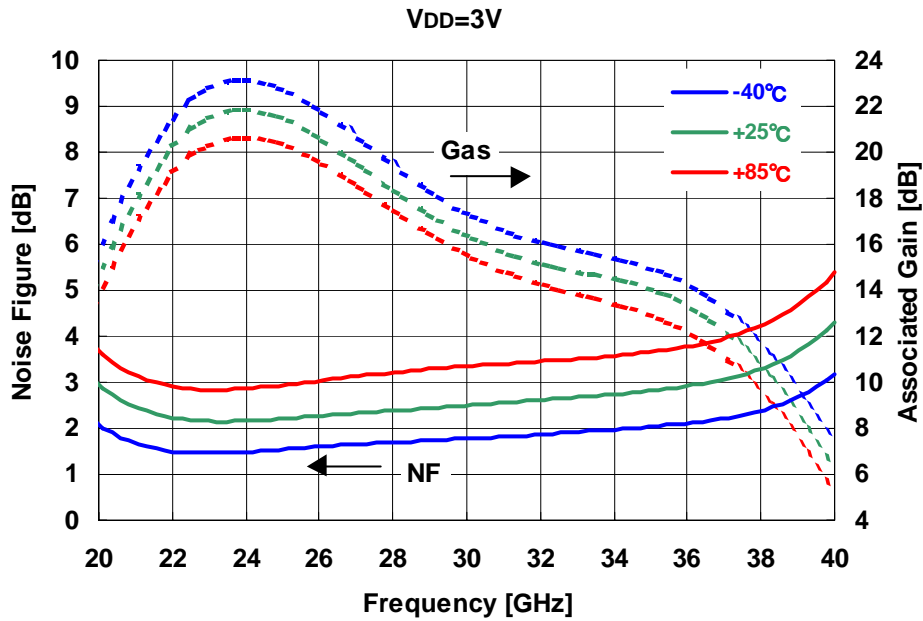
IMD PERFORMANCE  
vs. TOTAL OUTPUT POWER  
VDD=3V,  $\Delta f=+10\text{MHz}$



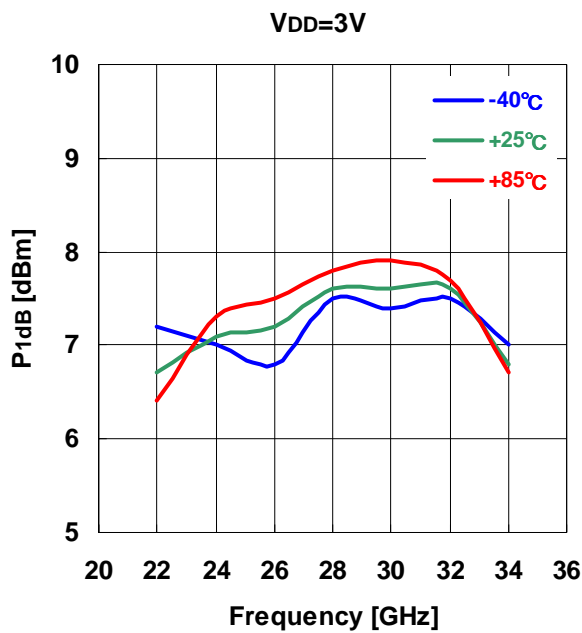
# FMM5703VZ

K / Ka Band Low Noise Amplifier MMIC

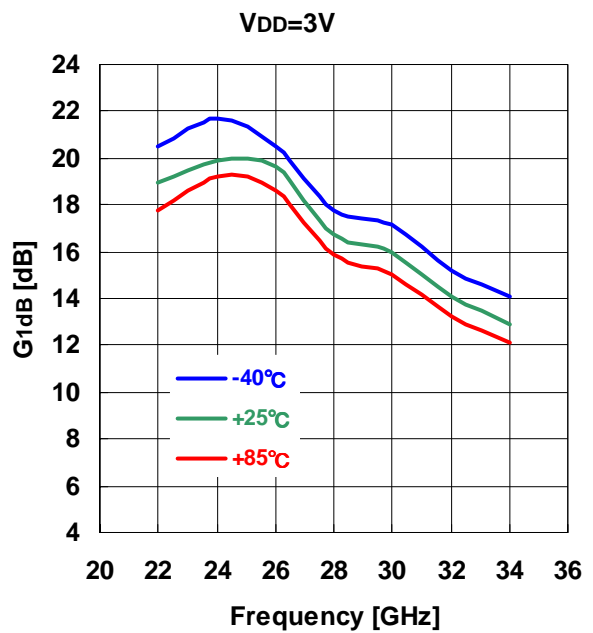
NOISE FIGURE, ASSOCIATED GAIN vs. FREQUENCY  
by Temperature



P1dB vs. FREQUENCY  
by Temperature



G1dB vs. FREQUENCY  
by Temperature

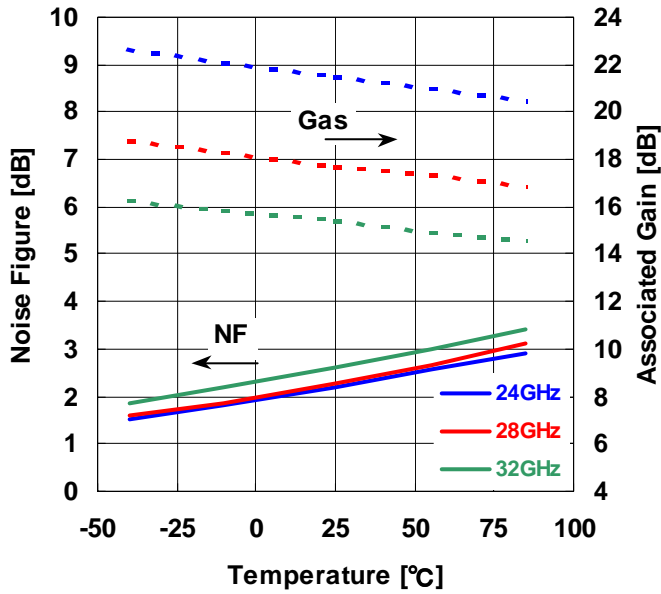


# FMM5703VZ

K / Ka Band Low Noise Amplifier MMIC

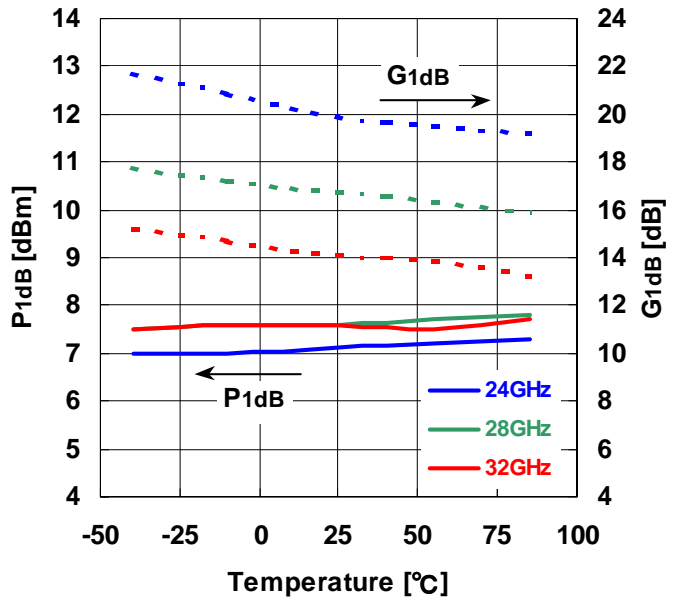
NOISE FIGURE, ASSOCIATED GAIN vs. TEMPERATURE

VDD=3V



P1dB, G1dB vs. TEMPERATURE

VDD=3V

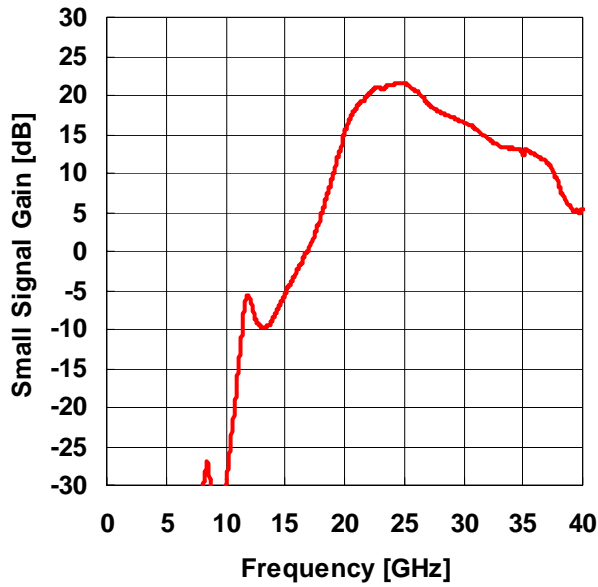


# FMM5703VZ

K / Ka Band Low Noise Amplifier MMIC

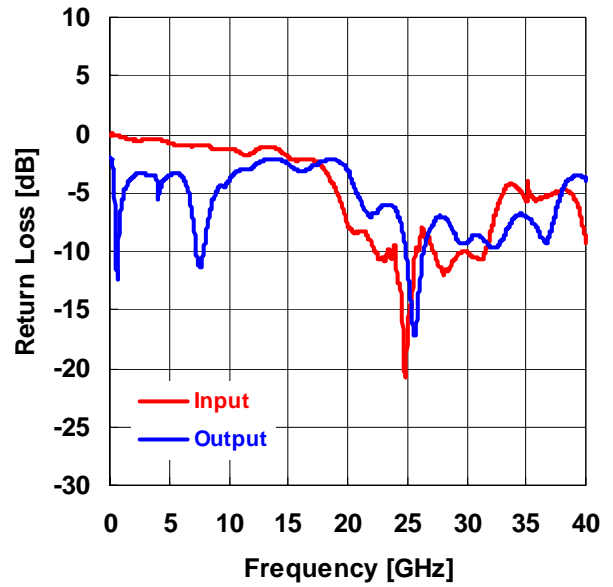
SMALL SIGNAL GAIN vs. FREQUENCY

VDD=3V



RETURN LOSS vs. FREQUENCY

VDD=3V



# FMM5703VZ

K / Ka Band Low Noise Amplifier MMIC

## ■ S-PARAMETER

VDD=3V

FREQ. [MHz]	S11		S21		S12		S22	
	mag.	ang.	mag.	ang.	mag.	ang.	mag.	ang.
1000	0.975	-64.1	0.001	-149.0	0.000	50.3	0.495	158.8
2000	0.943	-129.4	0.003	124.3	0.001	66.4	0.662	115.3
3000	0.945	179.3	0.004	46.1	0.001	-6.7	0.675	70.8
4000	0.947	131.4	0.008	50.3	0.005	74.4	0.575	1.0
5000	0.918	64.8	0.011	-92.3	0.004	-82.7	0.664	-49.6
6000	0.893	-7.6	0.011	-172.6	0.003	-151.9	0.669	-93.2
7000	0.889	-64.8	0.012	89.7	0.002	-168.7	0.432	-133.9
8000	0.899	-122.3	0.026	-41.0	0.002	170.8	0.343	-121.8
9000	0.861	178.8	0.018	157.0	0.000	108.9	0.573	-173.1
10000	0.868	121.4	0.032	146.1	0.005	37.8	0.636	137.4
11000	0.832	52.3	0.151	91.1	0.002	-58.8	0.702	90.2
12000	0.833	-17.0	0.506	-57.8	0.002	164.8	0.718	43.9
13000	0.883	-64.2	0.329	-151.0	0.004	95.2	0.773	5.5
14000	0.870	-104.8	0.368	150.9	0.004	40.3	0.783	-25.4
15000	0.797	-164.1	0.532	89.3	0.004	-26.2	0.746	-61.3
16000	0.781	131.3	0.750	24.2	0.003	-93.7	0.693	-113.7
17000	0.778	82.6	1.049	-37.5	0.002	22.1	0.728	-163.5
18000	0.710	30.9	1.662	-97.5	0.004	-38.3	0.771	165.2
19000	0.579	-43.0	2.984	-164.2	0.007	-109.4	0.777	140.9
20000	0.415	-149.7	5.653	116.3	0.006	-170.1	0.705	108.3
21000	0.387	75.0	8.317	23.2	0.003	-178.1	0.531	66.0
22000	0.347	-15.9	10.026	-63.7	0.007	157.9	0.449	16.5
23000	0.294	-126.7	11.080	-151.6	0.007	93.5	0.497	-50.6
24000	0.317	158.3	11.601	126.9	0.009	60.4	0.482	-119.8
25000	0.125	174.4	11.872	43.5	0.012	8.5	0.285	168.7
26000	0.321	-163.2	10.631	-37.6	0.014	-65.5	0.212	6.2
27000	0.333	161.6	8.870	-112.9	0.013	-134.4	0.400	-53.3
28000	0.254	110.9	7.785	-179.3	0.013	168.0	0.442	-84.4
29000	0.293	52.5	7.199	113.3	0.016	93.7	0.375	-134.8
30000	0.314	9.0	6.704	45.4	0.016	31.3	0.345	165.4
31000	0.292	-50.1	6.101	-23.3	0.019	-23.7	0.372	123.3
32000	0.374	-112.3	5.303	-89.1	0.027	-91.3	0.332	90.8
33000	0.554	-156.4	4.726	-151.9	0.030	-158.0	0.353	42.9
34000	0.604	160.2	4.587	145.4	0.028	146.8	0.439	-9.3
35000	0.519	106.4	4.271	79.0	0.033	101.9	0.444	-35.8
36000	0.526	29.4	4.163	10.7	0.042	43.3	0.395	-65.2
37000	0.548	-36.6	3.722	-59.5	0.043	-28.2	0.371	-152.5
38000	0.574	-109.2	2.667	-130.3	0.032	-82.8	0.564	148.5
39000	0.541	-157.3	1.937	177.5	0.031	-124.5	0.660	130.9
40000	0.356	166.3	1.855	126.3	0.035	-168.1	0.645	118.1

**Eudyna**

# FMM5703VZ

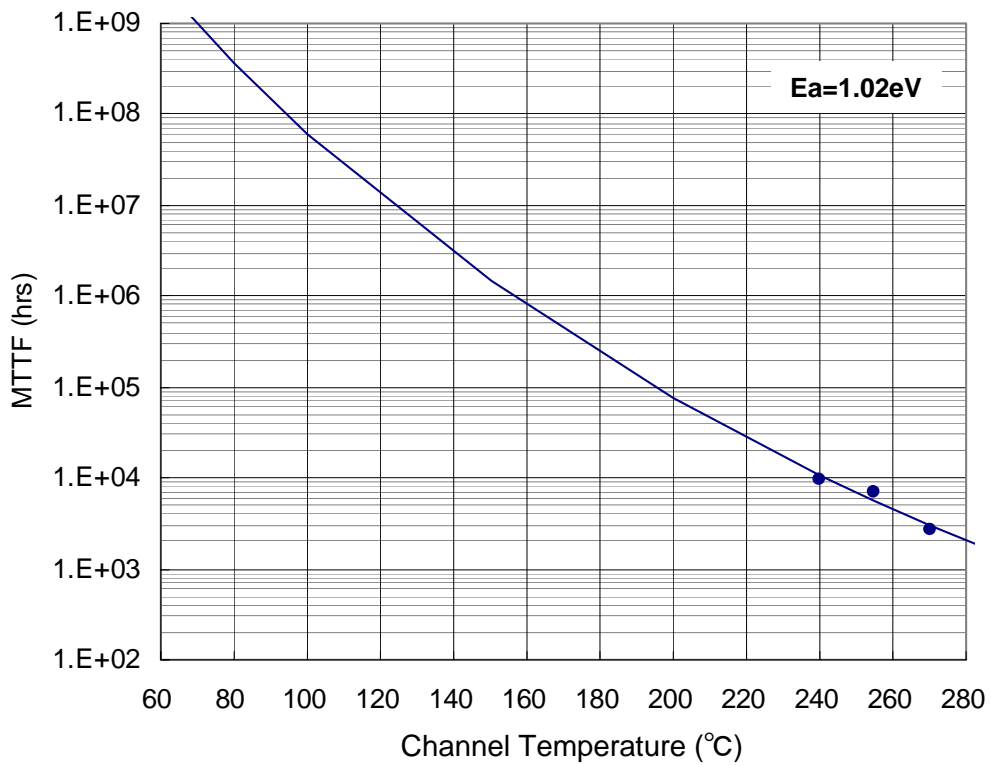
K / Ka Band Low Noise Amplifier MMIC

## THERMAL INFORMATION (REFERENCE DATA)

	V <sub>DD</sub> =3V, I <sub>DD</sub> =20mA	Unit
$\Delta T_{ch}$	7	°C

note)  $\Delta T_{ch}$ : BGA Package Balls to channel temperature rise

MTTF vs.  $\Delta T_{ch}$

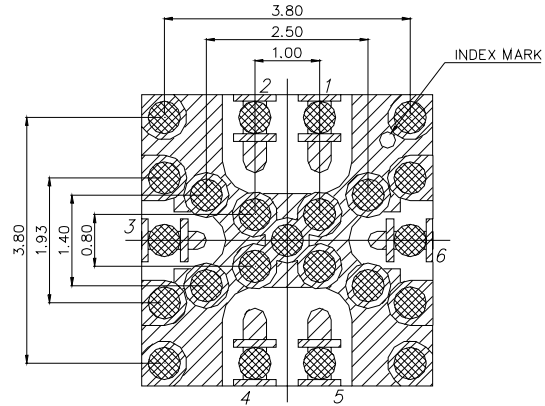
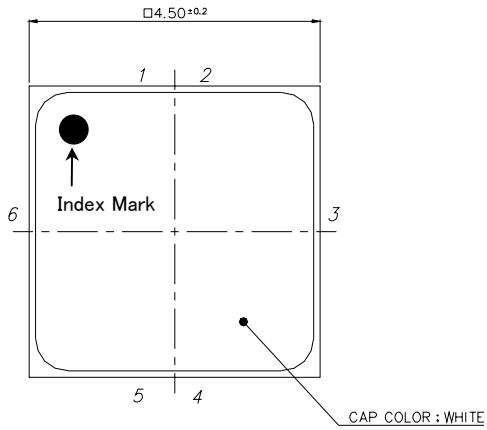




# FMM5703VZ

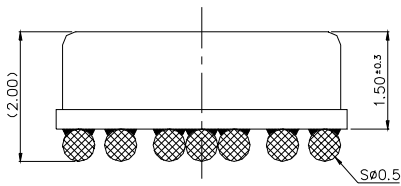
K / Ka Band Low Noise Amplifier MMIC

## Package Outline and Pin Assignment

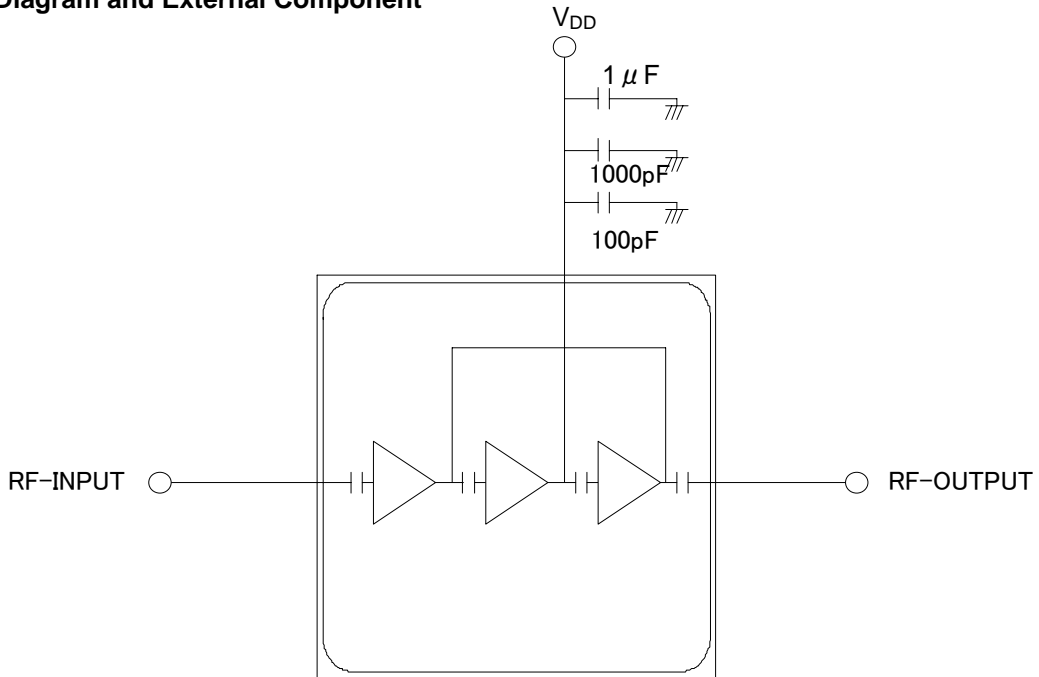


### PIN ASSIGNMENT

- 1: N.C.
- 2: VDD
- 3: RFout
- 4: N.C.
- 5: N.C.
- 6: RFin



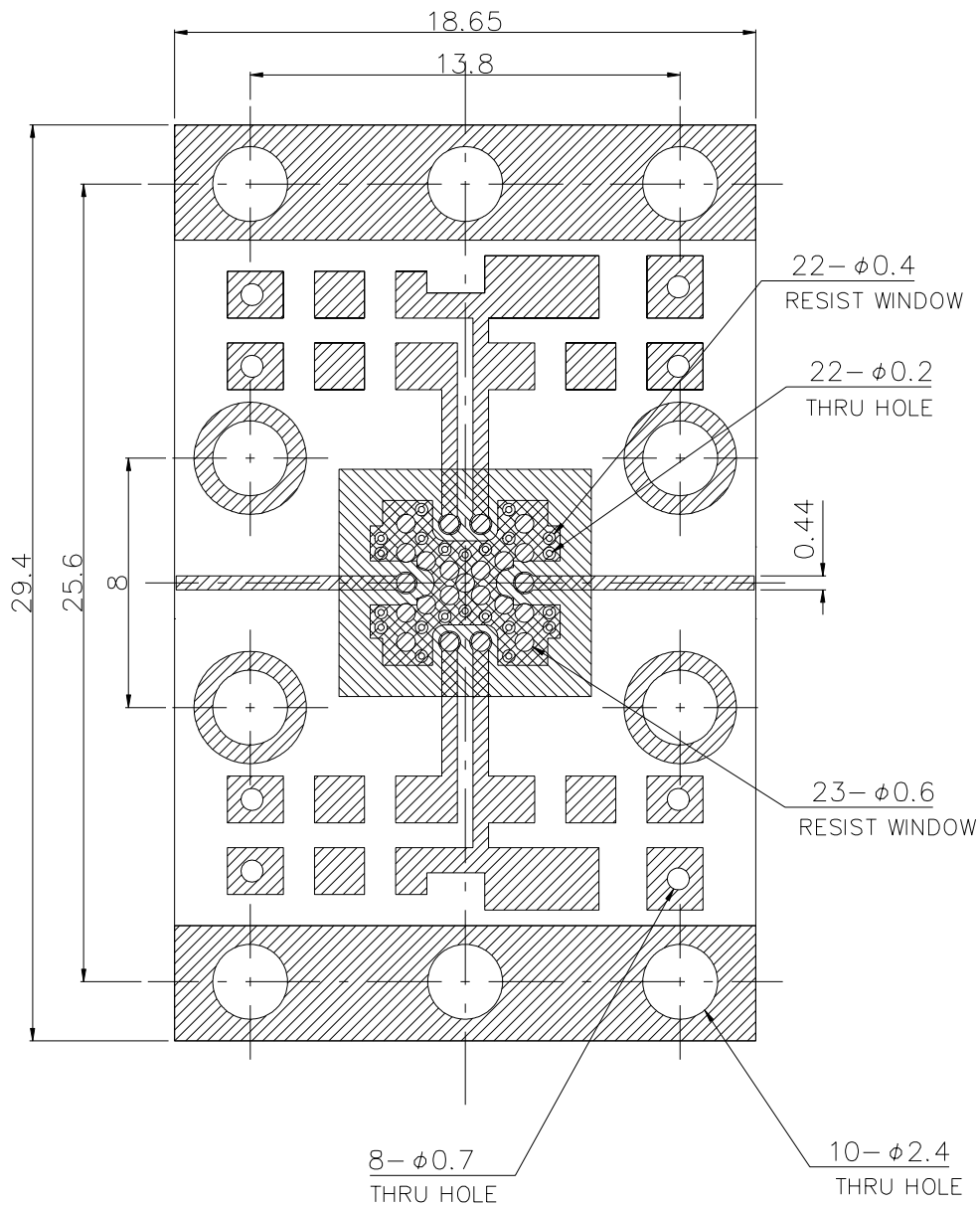
## Block Diagram and External Component





# FMM5703VZ

## K / Ka Band Low Noise Amplifier MMIC

### Recommended Foot Pattern Layout



Notes :

1. LAMINATE : Rogers Corporation RO4003  
Thickness  $t=0.2\text{mm}$ , Cu Foil  $18\ \mu\text{m}$
2.  : Finish to copper foil ; Ni  $0.1\ \mu\text{m}$  min./Au  $0.1\pm 0.08\ \mu\text{m}$  (Both side)
3.  : Resist

---

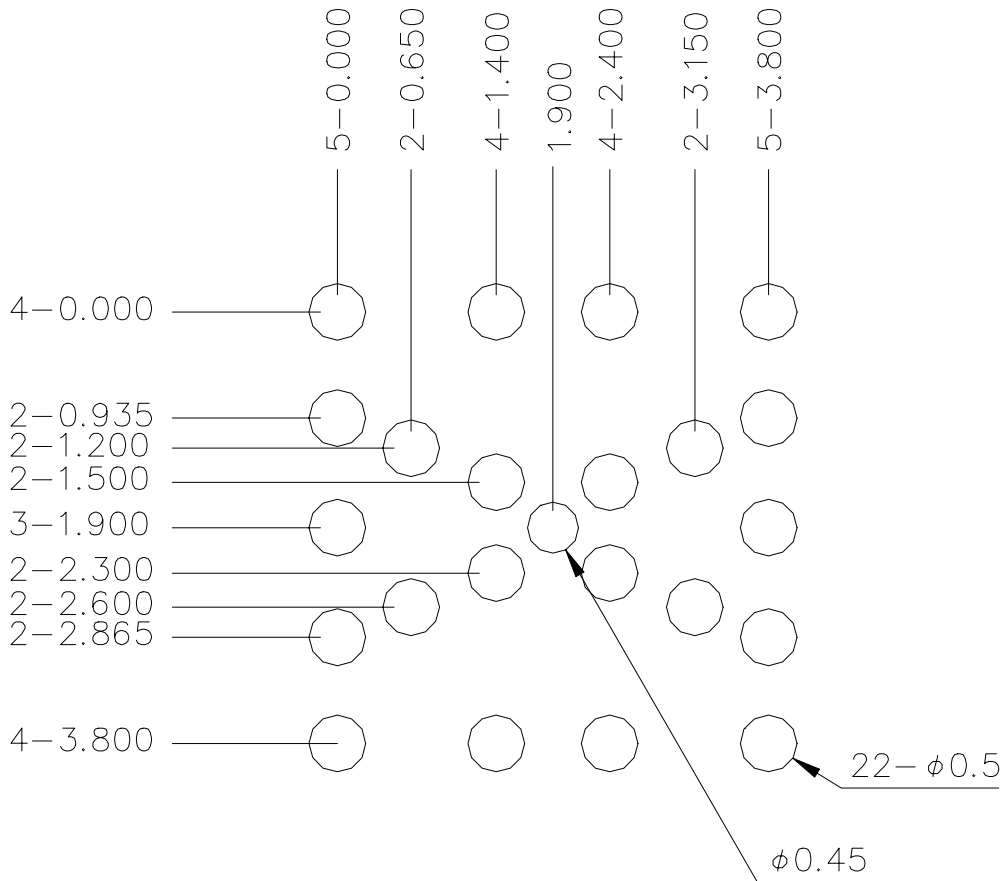
---

---

# FMM5703VZ

K / Ka Band Low Noise Amplifier MMIC

## ■ Recommended Stencil Pattern



Thickness : 0.15  $\mu$ m

# **FMM5703VZ**

## **K / Ka Band Low Noise Amplifier MMIC**

For further information please contact :

**Eudyna Devices USA Inc.**  
2355 Zanker Rd.  
San Jose, CA 95131-1138, U.S.A.  
TEL: (408) 232-9500  
FAX: (408) 428-9111  
www.us.eudyna.com

**Eudyna Devices Europe Ltd.**  
Network House  
Norreys Drive  
Maidenhead, Berkshire SL6 4FJ  
United Kingdom  
TEL: +44 (0) 1628 504800  
FAX: +44 (0) 1628 504888

**Eudyna Devices Asia Pte. Ltd.**  
Hong Kong Branch  
Rm.1101,Ocean Centre, 5 Canton Road  
Tsim Sha Tsui, Kowloon, Hong Kong  
TEL: +852-2377-0227  
FAX: +852-2377-3921

**Eudyna Devices Inc.**  
1000 Kamisukiahara, showa-cho  
Nakakomagun, Yamanashi  
409-3883, Japan  
(Kokubo Industrial Park)  
TEL +81-55-275-4411  
FAX +81-55-275-9461  
**Sales Division**  
1, Kanai-cho, Sakae-ku  
Yokohama, 244-0845, Japan  
TEL +81-45-853-8156  
FAX +81-45-853-8170

### **CAUTION**

Eudyna Devices Inc. products contain **gallium arsenide (GaAs)** which can be hazardous to the human body and the environment. For safety, observe the following procedures:

- Do not put these products into the mouth.
- Do not alter the form of this product into a gas, powder, or liquid through burning, crushing, or chemical processing as these by-products are dangerous to the human body if inhaled, ingested, or swallowed.
- Observe government laws and company regulations when discarding this product. This product must be discarded in accordance with methods specified by applicable hazardous waste procedures.

Eudyna Devices Inc. reserves the right to change products and specifications without notice. The information does not convey any license under rights of Eudyna Devices Inc. or others.

© 2004 Eudyna Devices USA Inc.  
Printed in U.S.A.

# **Eudyna**